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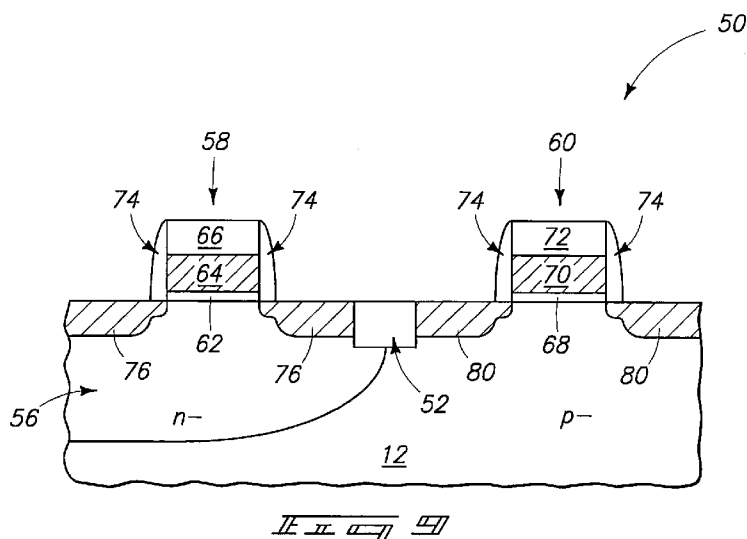
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(54) Title: METHODS UTILIZING MICROWAVE RADIATION DURING FORMATION OF SEMICONDUCTOR CONSTRUCTIONS



(57) Abstract: Some embodiments include methods in which microwave radiation is used to activate dopant and/or increase crystallinity of semiconductor material during formation of a semiconductor construction. In some embodiments, the microwave radiation has a frequency of about 5.8 gigahertz, and a temperature of the semiconductor construction does not exceed about 500°C during the exposure to the microwave radiation.